HongWen Jiang

List of Publications by Year
in descending order

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20	919	840119 11	839053 18
papers	citations	h-index	g-index

20	20	20	1025
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Spin transfer nano-oscillators. Nanoscale, 2013, 5, 2219.	2.8	167
2	Ultralow-current-density and bias-field-free spin-transfer nano-oscillator. Scientific Reports, 2013, 3, 1426.	1.6	162
3	High-Power Coherent Microwave Emission from Magnetic Tunnel Junction Nano-oscillators with Perpendicular Anisotropy. ACS Nano, 2012, 6, 6115-6121.	7.3	125
4	Giant spin-torque diode sensitivity in the absence of bias magnetic field. Nature Communications, 2016, 7, 11259.	5.8	123
5	Electron spin resonance and spinâ€“valley physics in a silicon double quantum dot. Nature Communications, 2014, 5, 3860.	5.8	82
6	Comparison of low frequency charge noise in identically patterned Si/SiO2 and Si/SiGe quantum dots. Applied Physics Letters, 2016, 108, .	1.5	66
7	Experimental Demonstration of Spintronic Broadband Microwave Detectors and Their Capability for Powering Nanodevices. Physical Review Applied, 2019, 11, .	1.5	49
8	Coherent manipulation of valley states at multiple charge configurations of a silicon quantum dot device. Nature Communications, 2017, 8, 64.	5.8	34
9	Two-axis quantum control of a fast valley qubit in silicon. Npj Quantum Information, 2019, 5, .	2.8	28
10	Photon-assisted-tunneling in a coupled double quantum dot under high microwave excitation powers. Applied Physics Letters, 2013, 103, .	1.5	25
11	Spin-Torque Driven Switching Probability Density Function Asymmetry. IEEE Transactions on Magnetics, 2012, 48, 3818-3820.	1.2	24
12	Back-action-induced non-equilibrium effect in electron charge counting statistics. Applied Physics Letters, 2012, 100, .	1.5	9
13	Thermal stability characterization of magnetic tunnel junctions using hard-axis magnetoresistance measurements. Journal of Applied Physics, 2011, 109, 07C708.	1.1	7
14	Direct Measurement of Electron Intervalley Relaxation in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Si</mml:mi><mml:mo>/</mml:mo><mml:mi>Si</mml:mi></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Ge</mml:mi></mml:math> Quantum Dot. Physical Review Applied, 2020, 14, .	1.5	6
15	High-Frequency Microwave Emission of a Trilayer Magnetic Tunnel Junction in the Absence of External Magnetic Bias Field. Physical Review Applied, 2020, 14, .	1.5	4
16	Observation of the Kondo effect in a quadruple quantum dot. Physical Review B, 2015, 91, .	1.1	3
17	Lifting of spin blockade by charged impurities in Si-MOS double quantum dot devices. Physical Review B, 2020, 101, .	1.1	3
18	Ultralow-current-density and bias-field-free spin-transfer nano-oscillator. , 0, .		1

#	Article	IF	Citations
19	Thermodynamic Compressibility Measurements in the Context of 2D Metalâ€“Insulator Transition. Journal of the Physical Society of Japan, 2003, 72, 49-52.	0.7	1
20	Efficient unitary method for simulation of driven quantum dot systems. Journal of Physics Communications, 2020, 4, 055004.	0.5	0